

### **isc** Silicon NPN Power Transistor

# 2SD728

#### DESCRIPTION

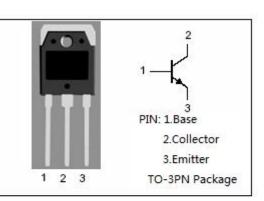
- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 100V(Min)
- Good Linearity of hFE
- Wide Area of Safe Operation
- Complement to Type 2SB692
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

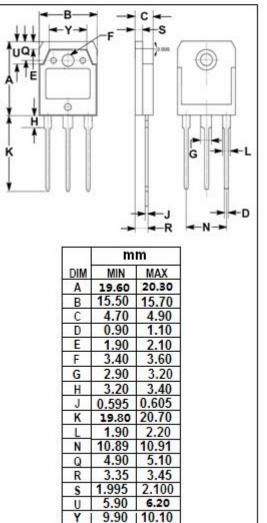
### **APPLICATIONS**

• Designed for low frequency power amplifier and power switching applications.

SYMBOL	PARAMETER	VALUE	UNIT					
V <sub>CBO</sub>	Collector-Base Voltage	150	V					
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V					
V <sub>EBO</sub>	Emitter-Base Voltage	V						
Ic	Collector Current-Continuous	ector Current-Continuous 6						
Pc	Collector Power Dissipation @ $T_C$ =25°C	70	W					
TJ	Junction Temperature	150	°C					
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C					

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)







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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	мах	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	100			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	150			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			1.5	V
V <sub>BE(on)</sub>	Base -Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> =0			50	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			100	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= 1A; Vc== 5V	40	100	200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	20			
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		160		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		7		MHz

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